W Walukiewicz

List of Publications by Year in Descending Order

254 papers	16,543 citations	62 h-index	124 g-index
257 ext. papers	17,599 ext. citations	3.4 avg, IF	6.1 L-index

#	Paper	IF	Citations
254	Conduction band modifications by d states in vanadium doped CdO. *Journal of Alloys and Compounds*, **2020**, 822, 153567	5.7	4
253	Effects of the host conduction band energy on the electronic band structure of ZnCdTeO dilute oxide alloys. *Journal of Applied Physics*, **2019**, 126, 083106	2.5	2
252	ZnO1−xTex highly mismatched alloys beyond the dilute alloy limit: Synthesis and electronic band structure. *Journal of Applied Physics*, **2019**, 125, 155702	2.5	7
251	Photoreflectance and photoinduced microwave reflectance studies of surface band bending in Mg-doped InN. *Journal of Applied Physics*, **2019**, 126, 045712	2.5	3
250	Growth of GaP1−x−yAsyNx on Si substrates by chemical beam epitaxy. *Journal of Applied Physics*, **2019**, 126, 105704	2.5	1
249	THz transient photoconductivity of the III-V dilute nitride GaP y As1−y−x N x. *Semiconductor Science and Technology*, **2018**, 33, 125009	1.8	1
248	Photoreflectance studies of optical transitions in GaNPAs intermediate band solar cell absorbers. *Solar Energy Materials and Solar Cells*, **2018**, 188, 99-104	6.4	4
247	Carrier Lifetimes in a III-V-N Intermediate-Band Semiconductor. *Physical Review Applied*, **2017**, 7,	4.3	5
246	Multicolor emission from intermediate band semiconductor ZnOSe. *Scientific Reports*, **2017**, 7, 44214	4.9	11
245	Effects of band anticrossing on the temperature dependence of the band gap of ZnSe1−xOxalloys. *Semiconductor Science and Technology*, **2017**, 32, 015005	1.8	5
244	Nitrogen-related intermediate band in P-rich GaNPAs alloys. *Scientific Reports*, **2017**, 7, 15703	4.9	11
243	Highly mismatched GaN1−xSbxalloys: synthesis, structure and electronic properties. *Semiconductor Science and Technology*, **2016**, 31, 083001	1.8	13
242	Undoped p-type GaN1−xSbx alloys: Effects of annealing. *Applied Physics Letters*, **2016**, 109, 252102	3.4	5
241	Effects of a semiconductor matrix on the band anticrossing in dilute group II-VI oxides. *Semiconductor Science and Technology*, **2015**, 30, 085018	1.8	14
240	InGaN pn-junctions grown by PA-MBE: Material characterization and fabrication of nanocolumn electroluminescent devices. *Journal of Crystal Growth*, **2015**, 425, 393-397	1.6	7
239	Effects of native defects on properties of low temperature grown, non-stoichiomtric gallium nitride. *Journal Physics D: Applied Physics*, **2015**, 48, 385101	3	5
238	Temperature evolution of carrier dynamics in GaNxPyAs1−x−yalloys. *Journal of Applied Physics*, **2015**, 117, 175702	2.5	15

237	Effects of the d-donor level of vanadium on the properties of Zn1−xVxO films. *Applied Physics Letters*, **2015**, 106, 182101	3.4	9
236	Growth and characterization of highly mismatched Zn1−xCdxTe1−yOy alloys for intermediate band solar cells **2015**,		1
235	Evidence of extreme type-III band offset at buried n-type CdO/p-type SnTe interfaces. *Physical Review B*, **2015**, 91,	3.3	7
234	Growth and characterization of ZnO1−xSx highly mismatched alloys over the entire composition. *Journal of Applied Physics*, **2015**, 118, 215702	2.5	36
233	Electronic band structure of highly mismatched GaN1−xSbx alloys in a broad composition range. *Applied Physics Letters*, **2015**, 107, 142104	3.4	23
232	Fabrication and characterization of multiband solar cells based on highly mismatched alloys. *Journal of Physics: Conference Series*, **2015**, 647, 012067	0.3	
231	Electronic band structure of ZnO-rich highly mismatched ZnO1−xTex alloys. *Applied Physics Letters*, **2015**, 106, 092101	3.4	24
230	Modeling of the atomic structure and electronic properties of amorphous GaN1−xAsx. *Computational Materials Science*, **2014**, 82, 100-106	3.2	12
229	Growth and characterization of highly mismatched GaN1−xSbx alloys. *Journal of Applied Physics*, **2014**, 116, 123704	2.5	18
228	Electronic Band Structure of GaNxPyAs1−x−y Highly Mismatched Alloys: Suitability for Intermediate-Band Solar Cells. *Physical Review Applied*, **2014**, 1,	4.3	60
227	Surface photovoltage and modulation spectroscopy of E− and E+ transitions in GaNAs layers. *Thin Solid Films*, **2014**, 567, 101-104	2.2	14
226	Composition and optical properties of dilute-Sb GaN1−xSbxhighly mismatched alloys grown by MBE. *Journal Physics D: Applied Physics*, **2014**, 47, 465102	3	9
225	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. *Applied Physics Letters*, **2013**, 102, 112105	3.4	32
224	Crystal structure and properties of CdxZn1−xO alloys across the full composition range. *Applied Physics Letters*, **2013**, 102, 232103	3.4	52
223	Highly mismatched N-rich GaN1−xSbx films grown by low temperature molecular beam epitaxy. *Applied Physics Letters*, **2013**, 102, 102104	3.4	24
222	Local structure of amorphous GaN1−xAsx semiconductor alloys across the composition range. *Journal of Applied Physics*, **2013**, 113, 243505	2.5	6
221	P-type InGaN across the entire alloy composition range. *Applied Physics Letters*, **2013**, 102, 102111	3.4	11
220	Temperature dependence of photoluminescence from InNAsSb layers: The role of localized and free carrier emission in determination of temperature dependence of energy gap. *Applied Physics Letters*, **2013**, 102, 122109	3.4	16

219	Correlations between the band structure, activation energies of electron traps, and photoluminescence in n-type GaNAs layers. *Applied Physics Letters*, **2012**, 101, 082109	3.4	18
218	Controlling the Curie temperature in (Ga,Mn)As through location of the Fermi level within the impurity band. *Nature Materials*, **2012**, 11, 444-9	27	148
217	Temperature dependence of E0 and E0 + ΔO transitions in In0.53Ga0.47BixAs1−x alloys studied by photoreflectance. *Journal of Applied Physics*, **2012**, 112, 113508	2.5	14
216	Engineering the electronic band structure for multiband solar cells. *Physical Review Letters*, **2011**, 106, 028701	7.4	225
215	Thermal stability of amorphous GaN1−xAsx alloys. *Applied Physics Letters*, **2011**, 98, 161902	3.4	7
214	Electronic structure of CdO studied by soft X-ray spectroscopy. *Journal of Electron Spectroscopy and Related Phenomena*, **2011**, 184, 249-253	1.7	22
213	Mg doped InN and confirmation of free holes in InN. *Applied Physics Letters*, **2011**, 98, 042104	3.4	41
212	Doping of GaN1−xAsx with high As content. *Journal of Applied Physics*, **2011**, 110, 093702	2.5	4
211	Effects of point defects on thermal and thermoelectric properties of InN. *Applied Physics Letters*, **2011**, 98, 012108	3.4	36
210	GaN1−xBix: Extremely mismatched semiconductor alloys. *Applied Physics Letters*, **2010**, 97, 141919	3.4	31
209	Fermi level stabilization energy in cadmium oxide. *Journal of Applied Physics*, **2010**, 107, 113706	2.5	54
208	Full multiple scattering analysis of XANES at the Cd L3 and O K edges in CdO films combined with a soft-x-ray emission investigation. *Physical Review B*, **2010**, 82,	3.3	36
207	Electronic structure of Ga1−xMnxAs analyzed according to hole-concentration-dependent measurements. *Physical Review B*, **2010**, 81,	3.3	43
206	Hole transport and photoluminescence in Mg-doped InN. *Journal of Applied Physics*, **2010**, 107, 113712	2.5	62
205	Low gap amorphous GaN1−xAsx alloys grown on glass substrate. *Applied Physics Letters*, **2010**, 97, 101906	3.4	16
204	Finite element simulations of compositionally graded InGaN solar cells. *Solar Energy Materials and Solar Cells*, **2010**, 94, 478-483	6.4	145
203	High quality InxGa1−xN thin films with x > 0.2 grown on silicon. *Physica Status Solidi (B): Basic Research*, **2010**, 247, 1747-1749	1.3	13
202	Highly mismatched crystalline and amorphous GaN1−xAsx alloys in the whole composition range. *Journal of Applied Physics*, **2009**, 106, 103709	2.5	54

201	Numerical simulations of novel InGaN solar cells **2009**,		2
200	MBE GROWTH AND CHARACTERIZATION OF Mg-DOPED III-NITRIDES ON SAPPHIRE. *Selected Topics in Electornics and Systems*, **2009**, 113-119	0	
199	Properties of native point defects in In1−xAlxN alloys. *Journal Physics D: Applied Physics*, **2009**, 42, 095406(3)		2
198	Determining surface Fermi level pinning position of InN nanowires using electrolyte gating. *Applied Physics Letters*, **2009**, 95, 173114	3.4	16
197	MBE GROWTH AND CHARACTERIZATION OF Mg-DOPED III-NITRIDES ON SAPPHIRE. *International Journal of High Speed Electronics and Systems*, **2009**, 19, 113-119	0.5	
196	Electrical and electrothermal transport in InN: The roles of defects. *Physica B: Condensed Matter*, **2009**, 404, 4862-4865	2.8	10
195	Temperature dependence of the band gap of ZnSe1−xOx. *Applied Physics Letters*, **2009**, 95, 151907	3.4	31
194	Electronic Properties of InN and InGaN **2009**, 377-417		
193	Chapter 3 Fermi Level Effects on Mn Incorporation in III-Mn-V Ferromagnetic Semiconductors. *Semiconductors and Semimetals*, **2008**, 82, 89-133	0.6	1
192	Electronic Band Structure of Highly Mismatched Semiconductor Alloys **2008**, 65-89		3
191	Formation of Mn-derived impurity band in III-Mn-V alloys by valence band anticrossing. *Physical Review B*, **2008**, 78,	3.3	41
190	Modeling of InGaN/Si tandem solar cells. *Journal of Applied Physics*, **2008**, 104, 024507	2.5	126
189	Band gap bowing parameter of In1−xAlxN. *Journal of Applied Physics*, **2008**, 104, 123501	2.5	62
188	Composition dependence of the hole mobility in GaSbxAs1−x. *Applied Physics Letters*, **2008**, 92, 162105	3.4	3
187	Probing and modulating surface electron accumulation in InN by the electrolyte gated Hall effect. *Applied Physics Letters*, **2008**, 93, 262105	3.4	29
186	Properties of Ga1−xMnxAs with high x (>0.1). *Journal of Applied Physics*, **2008**, 103, 07D136	2.5	19
185	Effects of donor doping on Ga1−xMnxAs. *Applied Physics Letters*, **2008**, 93, 262505	3.4	16
184	Band anticrossing in highly mismatched SnxGe1−x semiconducting alloys. *Physical Review B*, **2008**, 77,	3.3	59

183	Optimum nitride concentration in multiband III-N-V alloys for high efficiency ideal solar cells. *Applied Physics Letters*, **2008**, 93, 174109	3.4	17
182	Characterization of MG-doped InGaN and InALN alloys grown by MBE for solar applications. *Conference Record of the IEEE Photovoltaic Specialists Conference*, **2008**,		2
181	Metal-insulator transition by isovalent anion substitution in Ga1-xMnxAs: implications to ferromagnetism. *Physical Review Letters*, **2008**, 101, 087203	7.4	32
180	Low-temperature grown compositionally graded InGaN films. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1866-1869		16
179	Mg-doped InN and InGaN Photoluminescence, capacitance-voltage and thermopower measurements. *Physica Status Solidi (B): Basic Research*, **2008**, 245, 873-877	1.3	53
178	Energetic Beam Synthesis of Dilute Nitrides and Related Alloys **2008**, 1-34		
177	Effects of quantum confinement on the doping limit of semiconductor nanowires. *Nano Letters*, **2007**, 7, 1186-90	11.5	59
176	TEM studies of as-grown, irradiated and annealed InN films. *Physica B: Condensed Matter*, **2007**, 401-402, 646-649	2.8	7
175	p-type InN and In-rich InGaN. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 1820-1824	1.3	21
174	Synthesis of highly mismatched alloys using ion implantation and pulsed laser melting. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 261, 1150-1154	1.2	9
173	Towards identification of localized donor states in InN. *Semiconductor Science and Technology*, **2007** , 22, 1161-1164	1.8	3
172	High electron mobility InN. *Applied Physics Letters*, **2007**, 90, 162103	3.4	29
171	Compensating point defects in He+4-irradiated InN. *Physical Review B*, **2007**, 75,	3.3	41
170	Electron mobility in InN and III-N alloys. *Journal of Applied Physics*, **2007**, 102, 073705	2.5	46
169	Valence-band anticrossing in mismatched III-V semiconductor alloys. *Physical Review B*, **2007**, 75,	3.3	310
168	Effects of surface states on electrical characteristics of InN and In1-xGaxN. *Physical Review B*, **2007**, 76,	3.3	57
167	Native-defect-controlled n-type conductivity in InN. *Physica B: Condensed Matter*, **2006**, 376-377, 436-439	2.8	24
166	Defects and Self-Compensation in Semiconductors. *Springer Series in Materials Science*, **2006**, 35-54	0.9	4

165	Photoluminescence of energetic particle-irradiated InxGa1−xN alloys. *Applied Physics Letters*, **2006**, 88, 151101	3.4	12
164	Optical bleaching effect in InN epitaxial layers. *Applied Physics Letters*, **2006**, 88, 191109	3.4	20
163	Structure and electronic properties of InN and In-rich group III-nitride alloys. *Journal Physics D: Applied Physics*, **2006**, 39, R83-R99	3	211
162	Evidence for p-type doping of InN. *Physical Review Letters*, **2006**, 96, 125505	7.4	176
161	Multiband GaNAsP quaternary alloys. *Applied Physics Letters*, **2006**, 88, 092110	3.4	112
160	Dopants and defects in InN and InGaN alloys. *Journal of Crystal Growth*, **2006**, 288, 278-282	1.6	12
159	Native defects in InxGa1−xN alloys. *Physica B: Condensed Matter*, **2006**, 376-377, 432-435	2.8	8
158	Pressure-dependent photoluminescence study of ZnO nanowires. *Applied Physics Letters*, **2005**, 86, 153113	3.4	80
157	Strain-engineered ferromagnetic In1−xMnxAs films with in-plane easy axis. *Applied Physics Letters*, **2005**, 86, 112512	3.4	20
156	Fermi-level stabilization energy in group III nitrides. *Physical Review B*, **2005**, 71,	3.3	172
155	Effect of film thickness on the incorporation of Mn interstitials in Ga1−xMnxAs. *Applied Physics Letters*, **2005**, 86, 042102	3.4	27
154	Band Anticrossing and Related Electronic Structure in III-N-V Alloys **2005**, 325-359		5
153	Electron Transport Properties of InN. *Materials Research Society Symposia Proceedings*, **2005**, 892, 91		5
152	Effect of native defects on optical properties of InxGa1−xN alloys. *Applied Physics Letters*, **2005**, 87, 161905	3.4	18
151	On the crystalline structure, stoichiometry and band gap of InN thin films. *Applied Physics Letters*, **2005**, 86, 071910	3.4	97
150	Multiphonon resonance Raman scattering in InxGa1−xN. *Physical Review B*, **2005**, 72,	3.3	21
149	Group III-nitride Materials for High Efficiency Photoelectrochemical Cells. *Materials Research Society Symposia Proceedings*, **2005**, 884, 1		3
148	Electronic and Optical Properties of Energetic Particle-Irradiated In-rich InGaN. *Materials Research Society Symposia Proceedings*, **2005**, 864, 7101		1

147	Highly Mismatched Alloys for Intermediate Band Solar Cells. *Materials Research Society Symposia Proceedings*, **2005**, 865, 571		7
146	Mutual Passivation in Dilute GaNxAs1-x Alloys. *Materials Research Society Symposia Proceedings*, **2005**, 864, 811		
145	Fermi level effects on Mn incorporation in modulation-doped ferromagnetic III1−xMnxV heterostructures. *Journal of Physics Condensed Matter*, **2004**, 16, S5499-S5508	1.8	7
144	High quality InN/GaN heterostructures grown by migration enhanced metalorganic chemical vapor deposition. *Applied Physics Letters*, **2004**, 84, 1892-1894	3.4	52
143	Direct evidence of the Fermi-energy-dependent formation of Mn interstitials in modulation-doped Ga1−yAlyAs/Ga1−xMnxAs/Ga1−yAlyAs heterostructures. *Applied Physics Letters*, **2004**, 84, 4325-4327	3.4	16
142	Synthesis and optical properties of II-O-VI highly mismatched alloys. *Journal of Applied Physics*, **2004**, 95, 6232-6238	2.5	55
141	Effects of pressure on the band structure of highly mismatched Zn1−yMnyOxTe1−x alloys. *Applied Physics Letters*, **2004**, 84, 924-926	3.4	10
140	Effects of electron concentration on the optical absorption edge of InN. *Applied Physics Letters*, **2004**, 84, 2805-2807	3.4	210
139	Compositional Ordering in InxGa1-xN and its influence on optical properties. *Materials Research Society Symposia Proceedings*, **2004**, 831, 126		
138	Lattice location of Mn and fundamental Curie temperature limit in ferromagnetic Ga1−xMnxAs. *Nuclear Instruments & Methods in Physics Research B*, **2004**, 219-220, 636-641	1.2	5
137	Synthesis and properties of highly mismatched II□□VI alloys. *IEE Proceedings: Optoelectronics*, **2004**, 151, 452-459		3
136	Mutual passivation effects in highly mismatched group III□□N alloys. *IEE Proceedings: Optoelectronics*, **2004**, 151, 460-464		5
135	Diluted ZnMnTe oxide: a multi-band semiconductor for high efficiency solar cells. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 660-663	1.3	22
134	Oxygen induced band-gap reduction in ZnOxSe1−x alloys. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 603-606	1.3	6
133	Effects of hydrostatic pressure on optical properties of InN and In-rich group III-nitride alloys. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 3107-3112	1.3	5
132	Optical properties and electronic structure of InN and In-rich group III-nitride alloys. *Journal of Crystal Growth*, **2004**, 269, 119-127	1.6	145
131	Electronic effects determining the formation of ferromagnetic III1−xMnxV alloys during epitaxial growth. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 25, 171-180	3	25
130	Valence band hybridization in N-rich GaN1−xAsx alloys. *Physical Review B*, **2004**, 70,	3.3	76

129	Band anticrossing in dilute nitrides. *Journal of Physics Condensed Matter*, **2004**, 16, S3355-S3372	1.8	26
128	Diluted II-VI oxide semiconductors with multiple band gaps. *Physical Review Letters*, **2003**, 91, 246403	7.4	219
127	Band gaps of InN and group III nitride alloys. *Superlattices and Microstructures*, **2003**, 34, 63-75	2.8	137
126	Mutual passivation of group IV donors and isovalent nitrogen in diluted GaNxAs1- alloys. *Physica B: Condensed Matter*, **2003**, 340-342, 389-393	2.8	3
125	Universal bandgap bowing in group-III nitride alloys. *Solid State Communications*, **2003**, 127, 411-414	1.6	92
124	Temperature dependence of the fundamental band gap of InN. *Journal of Applied Physics*, **2003**, 94, 4457-4460	2.5	337
123	Superior radiation resistance of In1-GaxN alloys: Full-solar-spectrum photovoltaic material system. *Journal of Applied Physics*, **2003**, 94, 6477-6482	2.5	503
122	Band-gap bowing effects in BxGa1-As alloys. *Journal of Applied Physics*, **2003**, 93, 2696-2699	2.5	35
121	Effect of oxygen on the electronic band structure in ZnOxSe1- alloys. *Applied Physics Letters*, **2003**, 83, 299-301	3.4	70
120	Composition dependence of the hydrostatic pressure coefficients of the bandgap of ZnSe1-Tex alloys. *Physical Review B*, **2003**, 68,	3.3	16
119	Mutual passivation effects in Si-doped diluted InyGa1-As1-Nx alloys. *Physical Review B*, **2003**, 68,	3.3	14
118	Origin of the large band-gap bowing in highly mismatched semiconductor alloys. *Physical Review B*, **2003**, 67,	3.3	61
117	Mutual passivation of group IV donors and nitrogen in diluted GaNxAs1- alloys. *Applied Physics Letters*, **2003**, 83, 2844-2846	3.4	16
116	Pressure Dependence of Optical Transitions in In-rich Group III-Nitride Alloys. *Materials Research Society Symposia Proceedings*, **2003**, 798, 301		
115	Hydrostatic pressure dependence of the fundamental bandgap of InN and In-rich group III nitride alloys. *Applied Physics Letters*, **2003**, 83, 4963-4965	3.4	63
114	Enhancement of Curie temperature in Ga1-MnxAs/Ga1-AlyAs ferromagnetic heterostructures by Be modulation doping. *Applied Physics Letters*, **2003**, 83, 4220-4222	3.4	67
113	Synthesis of GaNxAs1- thin films by pulsed laser melting and rapid thermal annealing of N+-implanted GaAs. *Journal of Applied Physics*, **2003**, 94, 1043-1049	2.5	43
112	Curie temperature limit in ferromagnetic Ga1-MnxAs. *Physical Review B*, **2003**, 68,	3.3	83

111	Band anticrossing in highly mismatched group II-VI semiconductor alloys. *Journal of Electronic Materials*, **2002**, 31, 754-758	1.9	6
110	Mutual passivation of electrically active and isovalent impurities. *Nature Materials*, **2002**, 1, 185-9	27	51
109	Determination of free hole concentration in ferromagnetic Ga1−xMnxAs using electrochemical capacitance–voltage profiling. *Applied Physics Letters*, **2002**, 81, 844-846	3.4	44
108	Band anticrossing in highly mismatched III–V semiconductor alloys. *Semiconductor Science and Technology*, **2002**, 17, 860-869	1.8	262
107	Current status of research and development of III–N–V semiconductor alloys. *Semiconductor Science and Technology*, **2002**, 17, 741-745	1.8	57
106	Enhanced nitrogen incorporation by pulsed laser annealing of GaNxAs1−x formed by N ion implantation. *Applied Physics Letters*, **2002**, 80, 3958-3960	3.4	27
105	Effect of the location of Mn sites in ferromagnetic Ga1−xMnxAs on its Curie temperature. *Physical Review B*, **2002**, 65,	3.3	461
104	Small band gap bowing in In1−xGaxN alloys. *Applied Physics Letters*, **2002**, 80, 4741-4743	3.4	498
103	Unusual properties of the fundamental band gap of InN. *Applied Physics Letters*, **2002**, 80, 3967-3969	3.4	1254
102	Band structure of highly mismatched semiconductor alloys: Coherent potential approximation. *Physical Review B*, **2002**, 65,	3.3	61
101	Transport-to-quantum lifetime ratios in AlGaN/GaN heterostructures. *Applied Physics Letters*, **2002**, 80, 2508-2510	3.4	34
100	Acoustic phonon scattering of two-dimensional electrons in GaN/AlGaN heterostructures. *Applied Physics Letters*, **2002**, 80, 1228-1230	3.4	46
99	Band anticrossing in GaP1−xNx alloys. *Physical Review B*, **2002**, 65,	3.3	62
98	Effects of the narrow band gap on the properties of InN. *Physical Review B*, **2002**, 66,	3.3	346
97	Band anticrossing in group II-Ox–VI1−x highly mismatched alloys: Cd1−xMnyOxTe1−x quaternaries synthesized by O ion implantation. *Applied Physics Letters*, **2002**, 80, 1571-1573	3.4	30
96	Band anticrossing effects in MgyZn1−yTe1−xSex alloys. *Applied Physics Letters*, **2002**, 80, 34-36	3.4	13
95	Intrinsic limitations to the doping of wide-gap semiconductors. *Physica B: Condensed Matter*, **2001**, 302-303, 123-134	2.8	279
94	Effects of structural defects on the activation of sulfur donors in GaNxAs1−x formed by N implantation. *Physica B: Condensed Matter*, **2001**, 308-310, 874-876	2.8	

93	Band Anticrossing in III□N□V Alloys. *Physica Status Solidi (B): Basic Research*, **2001**, 223, 75-85	1.3	107
92	Effect of polarization fields on transport properties in AlGaN/GaN heterostructures. *Journal of Applied Physics*, **2001**, 89, 1783	2.5	119
91	Formation of diluted III□V nitride thin films by N ion implantation. *Journal of Applied Physics*, **2001**, 90, 2227-2234	2.5	37
90	Influence of microstructure on electrical properties of diluted GaNxAs1□ formed by nitrogen implantation. *Applied Physics Letters*, **2001**, 79, 931-933	3.4	12
89	Synthesis of InNxP1□ thin films by N ion implantation. *Applied Physics Letters*, **2001**, 78, 1077-1079	3.4	39
88	Band structure and optical properties of InyGa1□As1□Nx alloys. *Physical Review B*, **2001**, 65,	3.3	58
87	Calculation of the ground state of shallow donors in GaAs1□Nx. *Journal of Applied Physics*, **2001**, 89, 789-791	2.5	5
86	Effect of band anticrossing on the optical transitions in GaAs1□Nx/GaAs multiple quantum wells. *Physical Review B*, **2001**, 64,	3.3	80
85	Synthesis of III-Nx-V1-x Thin Films by N Ion Implantation. *Materials Research Society Symposia Proceedings*, **2000**, 650, 1331		
84	synthesis of III-Nx-V1-x Thin Films by N Ion Implantation. *Materials Research Society Symposia Proceedings*, **2000**, 647, 1		
83	Large disparity between gallium and antimony self-diffusion in gallium antimonide. *Nature*, **2000**, 408, 69-72	50.4	90
82	Nitrogen-induced enhancement of the free electron concentration in sulfur implanted GaNxAs1□. *Applied Physics Letters*, **2000**, 77, 2858-2860	3.4	27
81	Effect of nitrogen on the electronic band structure of group III-N-V alloys. *Physical Review B*, **2000**, 62, 4211-4214	3.3	89
80	Role of nitrogen in the reduced temperature dependence of band-gap energy in GaNAs. *Applied Physics Letters*, **2000**, 77, 3021-3023	3.4	105
79	Increased electrical activation in the near-surface region of sulfur and nitrogen coimplanted GaAs. *Applied Physics Letters*, **2000**, 77, 3607-3609	3.4	12
78	Interaction of localized electronic states with the conduction band: band anticrossing in II-VI semiconductor ternaries. *Physical Review Letters*, **2000**, 85, 1552-5	7.4	162
77	Nitrogen-induced increase of the maximum electron concentration in group III-N-V alloys. *Physical Review B*, **2000**, 61, R13337-R13340	3.3	60
76	Large, nitrogen-induced increase of the electron effective mass in InyGa1□NxAs1□. *Applied Physics Letters*, **2000**, 76, 2409-2411	3.4	212

75	Nature of the fundamental band gap in GaNxP1− alloys. *Applied Physics Letters*, **2000**, 76, 3251-3253	3.4	211
74	Theoretical transport studies of p-type GaN/AlGaN modulation-doped heterostructures. *Applied Physics Letters*, **1999**, 74, 2405-2407	3.4	36
73	Dependence of the fundamental band gap of AlxGa1−N on alloy composition and pressure. *Journal of Applied Physics*, **1999**, 85, 8505-8507	2.5	100
72	Local structures of Ga atoms in amorphous silicon and hydrogenated amorphous silicon before and after synchrotron x-ray irradiation. *Applied Physics Letters*, **1999**, 75, 3282-3284	3.4	2
71	Effect of Nitrogen-Induced Modification of the Conduction Band Structure on Electron Transport in GaAsN Alloys. *Physica Status Solidi (B): Basic Research*, **1999**, 216, 135-139	1.3	56
70	Band Anticrossing in GaInNAs Alloys. *Physical Review Letters*, **1999**, 82, 1221-1224	7.4	1359
69	Reduction of band-gap energy in GaNAs and AlGaNAs synthesized by N+ implantation. *Applied Physics Letters*, **1999**, 75, 1410-1412	3.4	90
68	Effect of nitrogen on the band structure of GaInNAs alloys. *Journal of Applied Physics*, **1999**, 86, 2349-2351	2.5	130
67	Optical properties of InxGa1−N alloys grown by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **1998**, 84, 4452-4458	2.5	127
66	Near-band-edge photoluminescence emission in AlxGa1−N under high pressure. *Applied Physics Letters*, **1998**, 72, 2274-2276	3.4	12
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